

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	9mΩ @ V _{GS} = -4.5V	-13A
	11mΩ @ V _{GS} = -2.5V	-12A
	16mΩ @ V _{GS} = -1.8V	-10A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

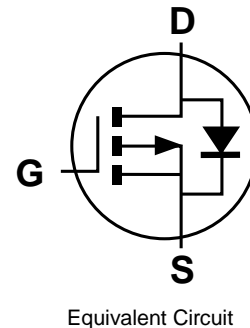
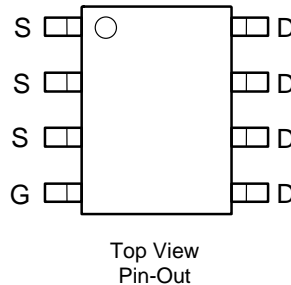
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power-management applications.

- Load switches
- Power-management functions

Mechanical Data

- Package: SO-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.074 grams (Approximate)

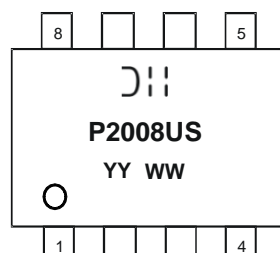


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP2008USS-13	SO-8	2500	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



D = Manufacturer's Marking
 P2008US = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 23 = 2023)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	T _A = +25°C	I _D	-13	A
		T _A = +70°C		-10	
		T _C = +25°C		-38	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-110	A
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I _{SM}	-110	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-3.7	A
Avalanche Current (Note 7)			I _{AS}	-49	A
Avalanche Energy (Note 7)			E _{AS}	119	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	87	°C/W
Total Power Dissipation (Note 6)	Steady State	P _D	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	54	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	7	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DSON}	—	6.5	9	mΩ	V _{GS} = -4.5V, I _D = -12A
		—	8.4	11		V _{GS} = -2.5V, I _D = -11A
		—	11.2	16		V _{GS} = -1.8V, I _D = -9A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -10A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iSS}	—	6820	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oSS}	—	622	—		
Reverse Transfer Capacitance	C _{rSS}	—	589	—		
Gate Resistance	R _g	—	2.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	76	—	nC	V _{DS} = -10V, I _D = -12A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	159	—		
Gate-Source Charge	Q _{gs}	—	6.9	—		
Gate-Drain Charge	Q _{gd}	—	15.6	—		
Turn-On Delay Time	t _{D(ON)}	—	22	—	ns	V _{GS} = -4.5V, V _{DS} = -10V, R _G = 6Ω, I _D = -12A
Turn-On Rise Time	t _r	—	33	—		
Turn-Off Delay Time	t _{D(OFF)}	—	291	—		
Turn-Off Fall Time	t _f	—	124	—		
Reverse Recovery Time	t _{RR}	—	25	—	ns	I _F = -12A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	16	—	nC	I _F = -12A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

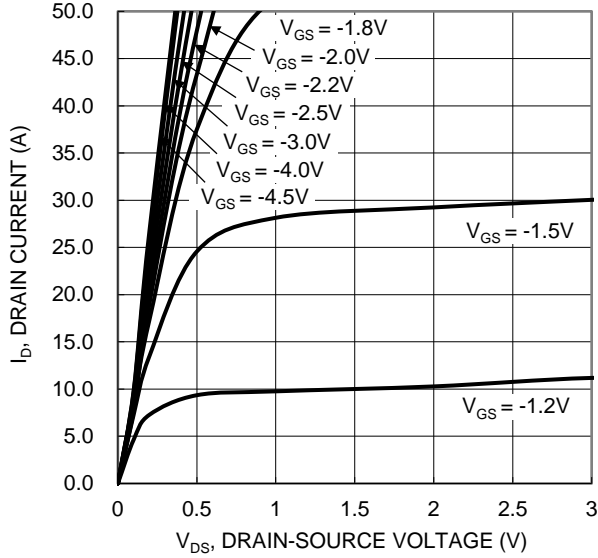


Figure 1. Typical Output Characteristic

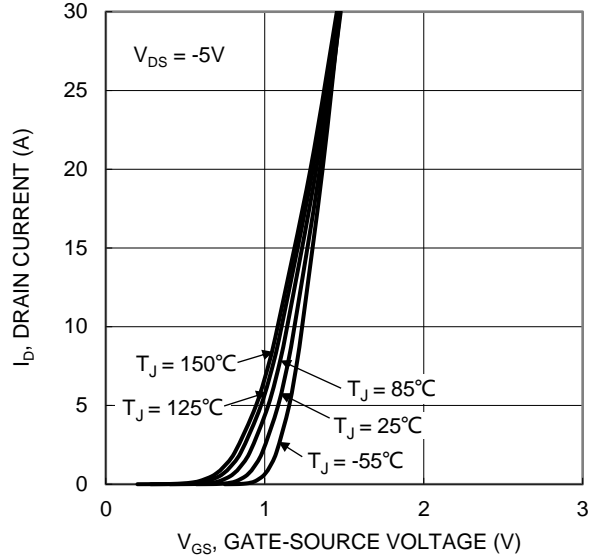


Figure 2. Typical Transfer Characteristic

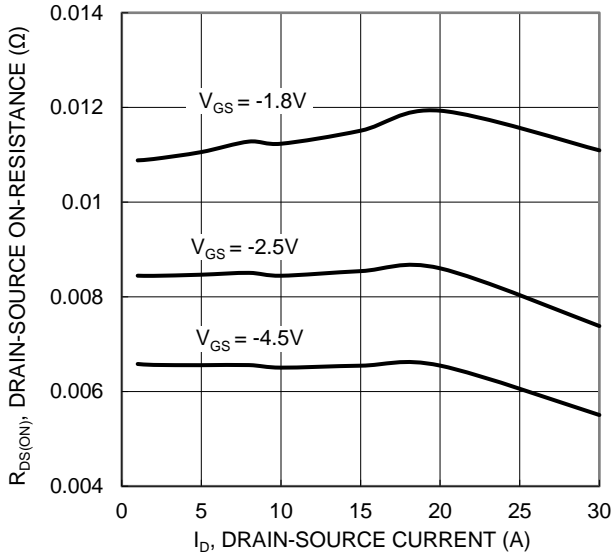


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

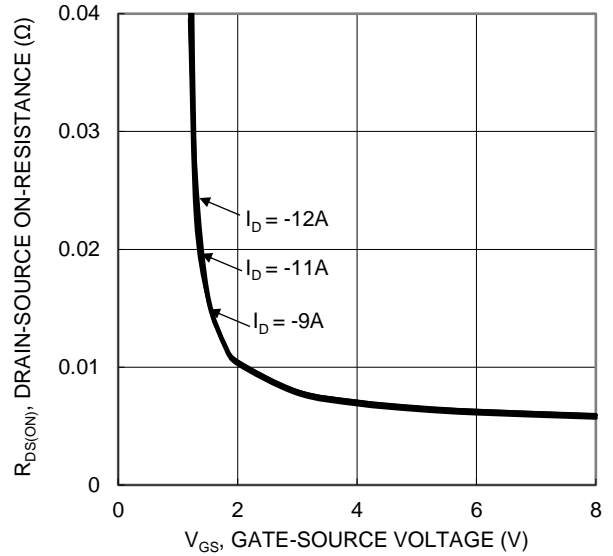


Figure 4. Typical Transfer Characteristic

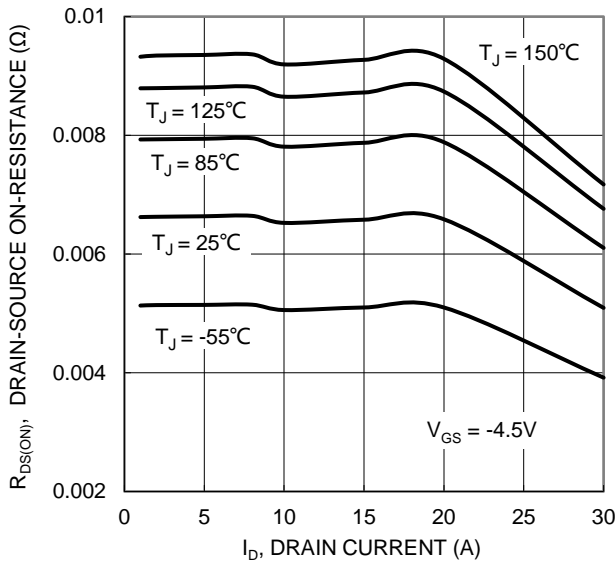


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

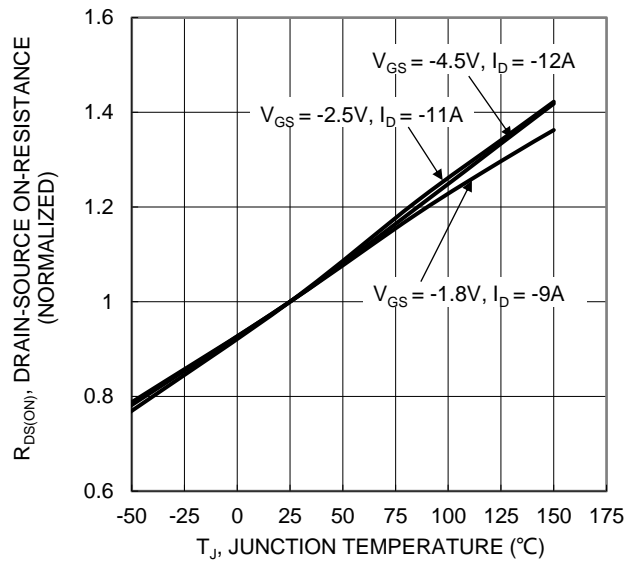


Figure 6. On-Resistance Variation with Junction Temperature

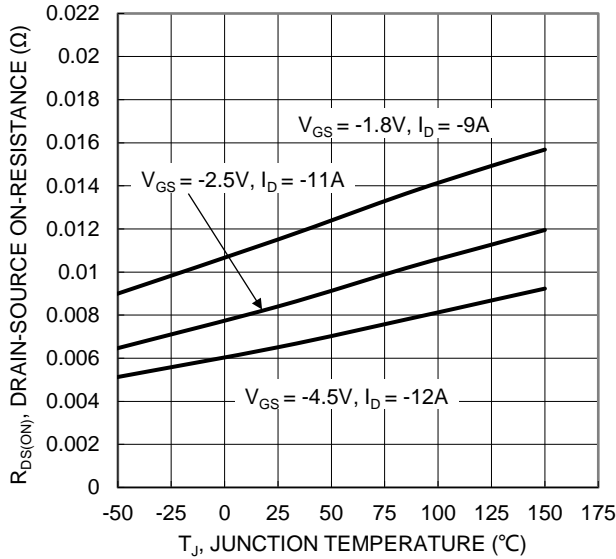


Figure 7. On-Resistance Variation with Junction Temperature

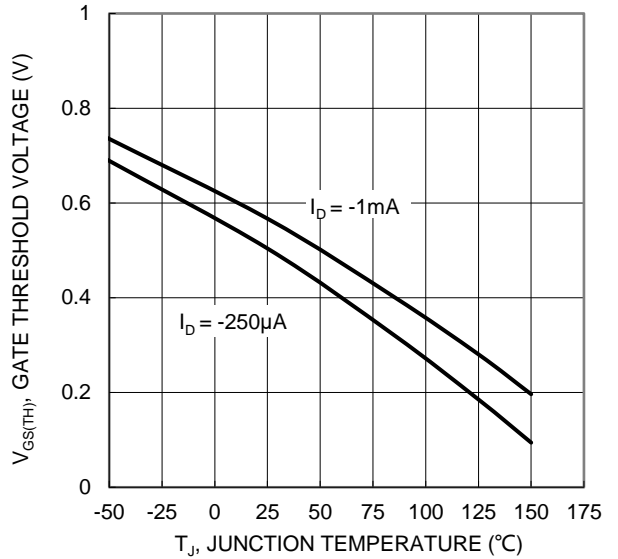


Figure 8. Gate Threshold Variation vs. Junction Temperature

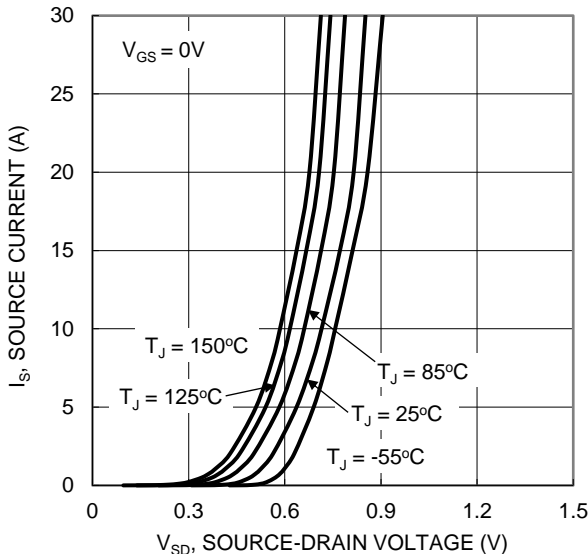


Figure 9. Diode Forward Voltage vs. Current

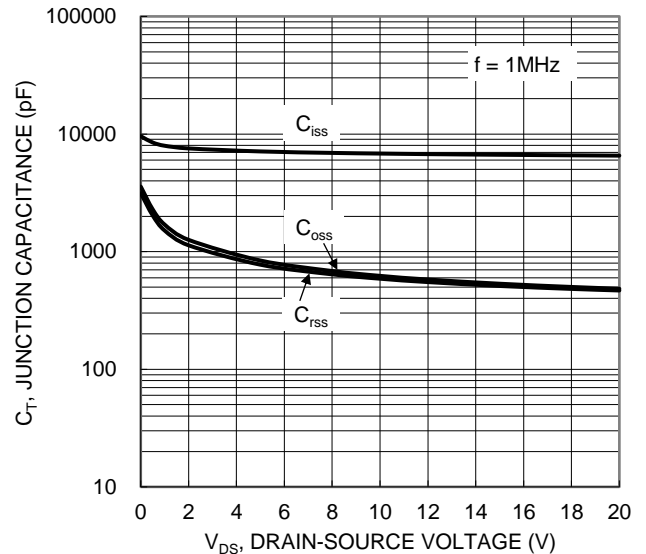


Figure 10. Typical Junction Capacitance

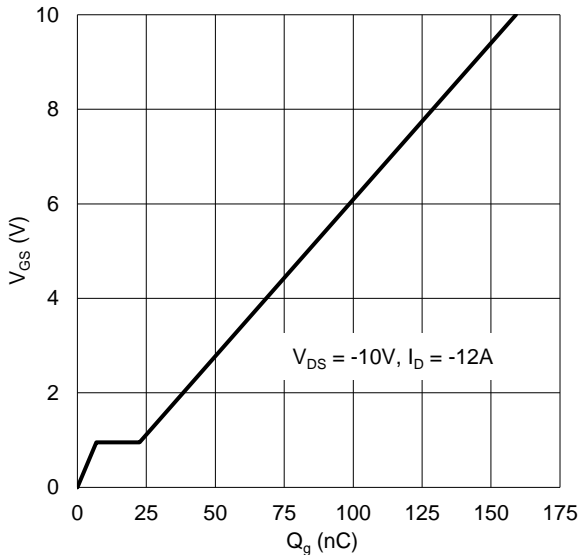


Figure 11. Gate Charge

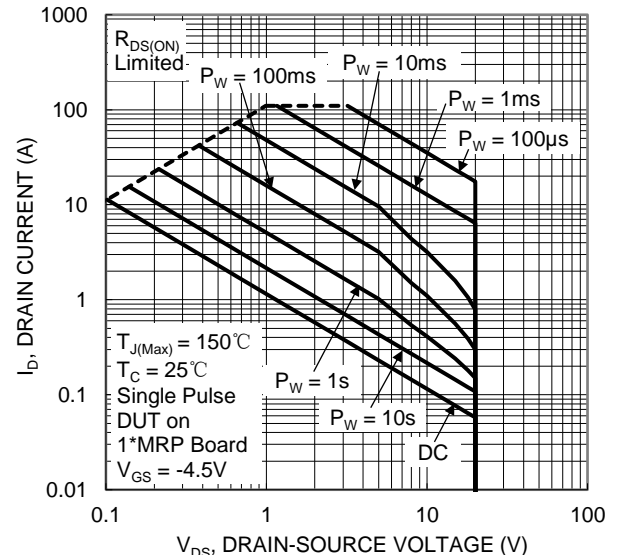


Figure 12. SOA, Safe Operation Area

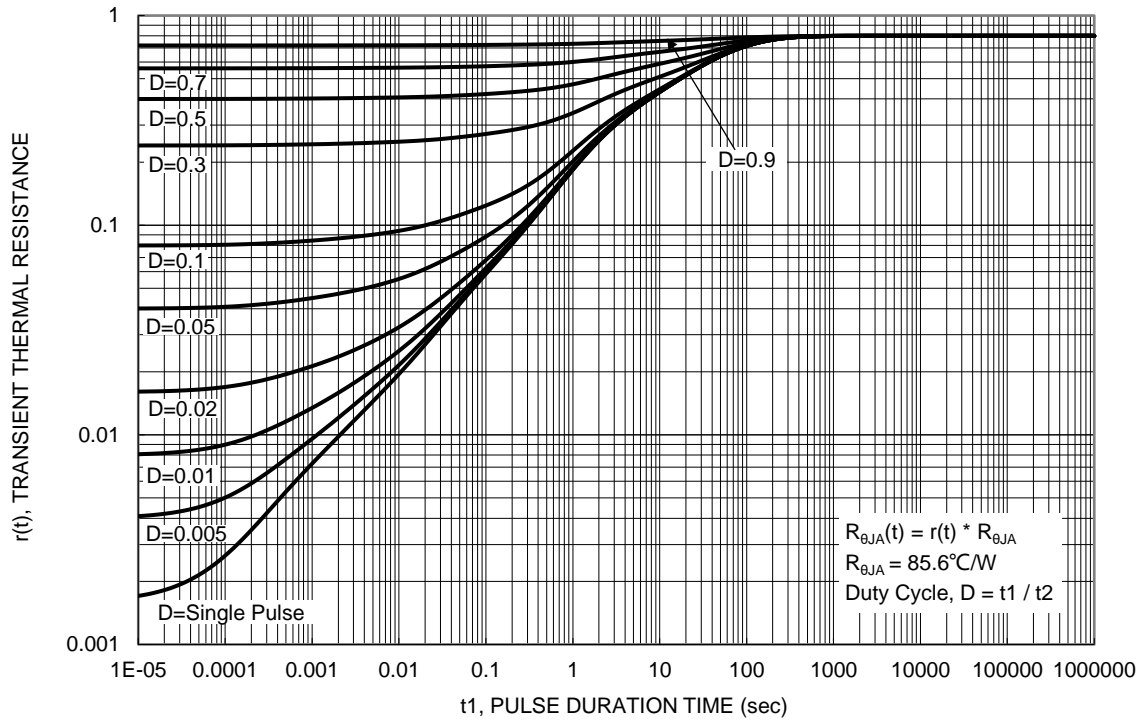
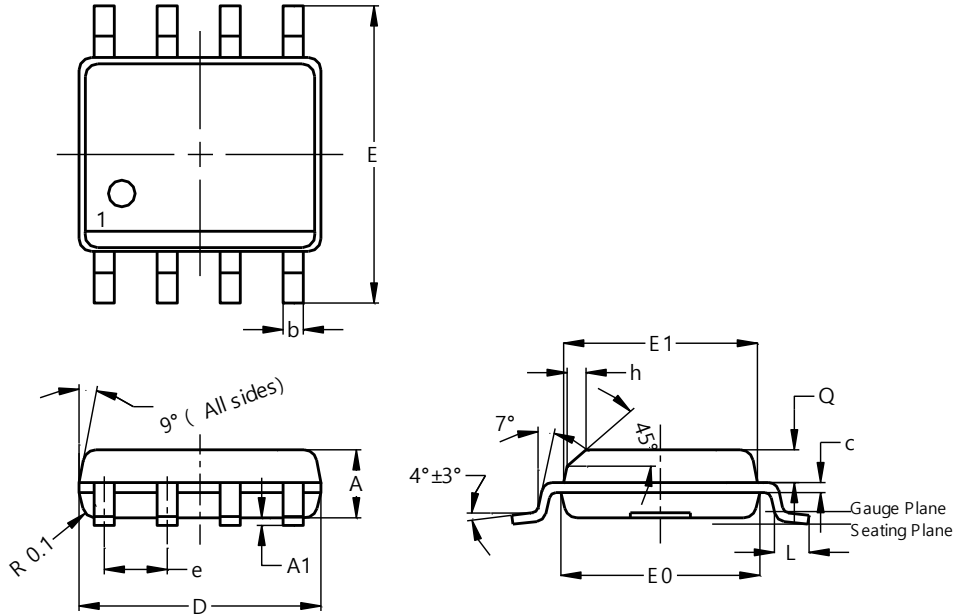


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

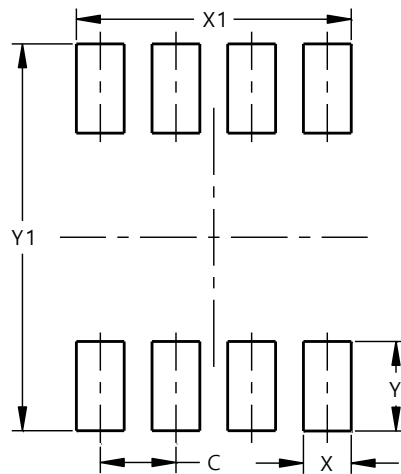


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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